

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	Martin Dauelsberg
Serial No. 10/	Filing Date: June 23, 2003
Title of Application:	Method For Depositing In Particular Crystalline Layers

Commissioner for Patents  
Post Office Box 1450  
Alexandria, VA 22313-1450

**Preliminary Amendment**

Dear Sir:

Please enter this preliminary amendment before examination of this case.

**Version with Markings to Show Changes Made to the Claims****In the Claims:**

1. (Amended) Method for depositing in particular crystalline layers on in particular crystalline substrates in a process chamber [(1)] of a reactor housing with a water-cooled wall [(2)], the base [(3)] of the process chamber [(1)] being heated, and one or more reaction gases being introduced centrally into the process chamber [(1)] as process gas, together with hydrogen as carrier gas, and being discharged through a gas outlet ring [(5)] which surrounds the process chamber [(1)], a purge gas [(7)] flowing between reactor cover [(6)] and processing chamber ceiling [(4)], which purge gas [(7)], together with a purge gas [(8)] which purges the space [(12)] between reactor wall [(2)] and gas outlet ring [(5)], is passed through a gap [(9)] between reactor ceiling [(4)] and the gas outlet ring [(5)], which can be lowered to allow loading of the process chamber [(1)], into the outer region [(1')] of the process chamber [(1)], in order to be sucked into the gas outlet ring [(54)] together with the process gas [(10)] through openings [(11)], the gas which purges the space [(12)] between reactor wall [(2)] and gas outlet ring [(5)] being nitrogen or a mixture of hydrogen and nitrogen.

2. Device for depositing in particular crystalline layers on in particular crystalline substrates in a process chamber [(1)] of a reactor housing with a water-cooled wall